

RT2N62M

Composite Transistor
For Muting Application
Silicon NPN Epitaxial Type

DESCRIPTION

RT2N62M is a composite transistor with built-in bias resistor

FEATURE

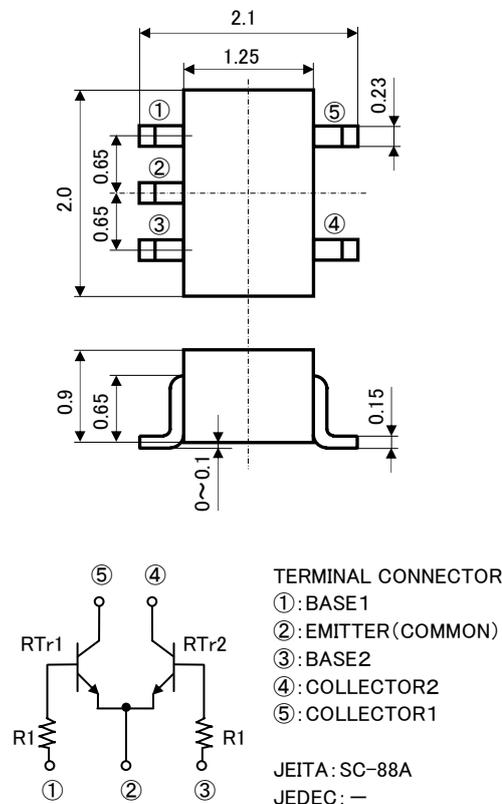
- Built-in bias resistor ($R_i=2.2\text{ k}\Omega$)
- Mini package for easy mounting

APPLICATION

muting circuit, switching circuit

OUTLINE DRAWING

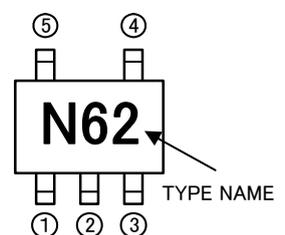
Unit:mm



MAXIMUM RATINGS (Ta=25°C) (RTTr1, RTTr2 Common)

| Symbol | Parameter | Ratings | Unit |
|-----------|------------------------------|----------|------|
| V_{CBO} | Collector to Base voltage | 40 | V |
| V_{EBO} | Emitter to Base voltage | 40 | V |
| V_{CEO} | Collector to Emitter voltage | 20 | V |
| I_C | Collector current | 400 | mA |
| P_T | Total dissipation | 150 | mW |
| T_j | Junction temperature | +150 | °C |
| T_{stg} | Storage temperature | -55~+150 | °C |

MARKING



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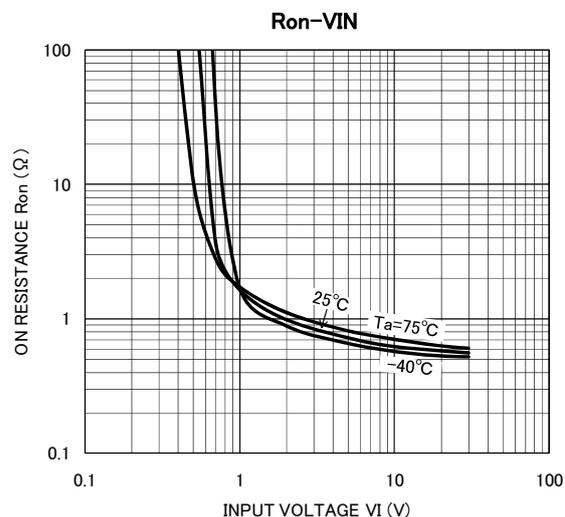
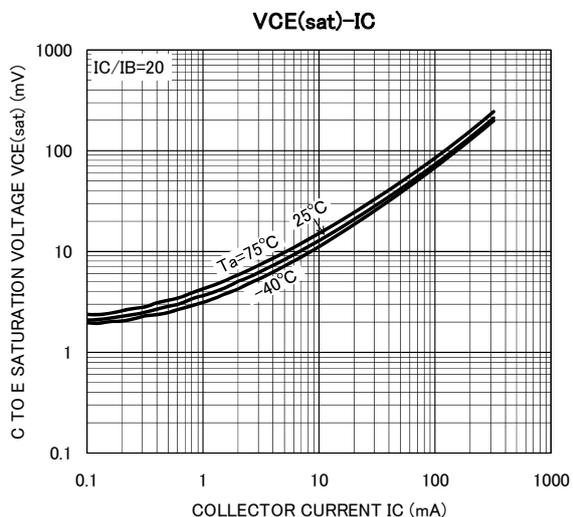
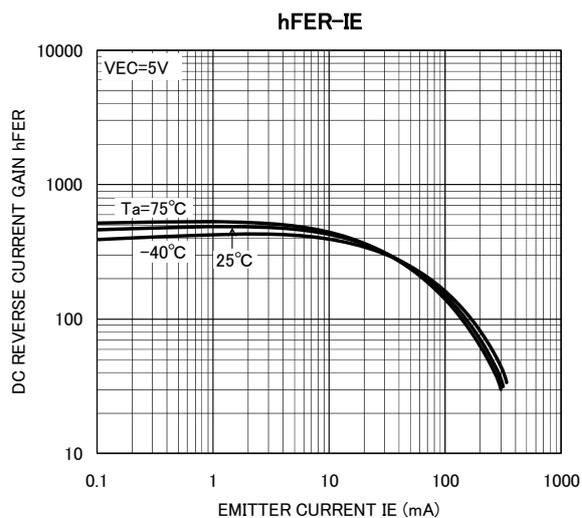
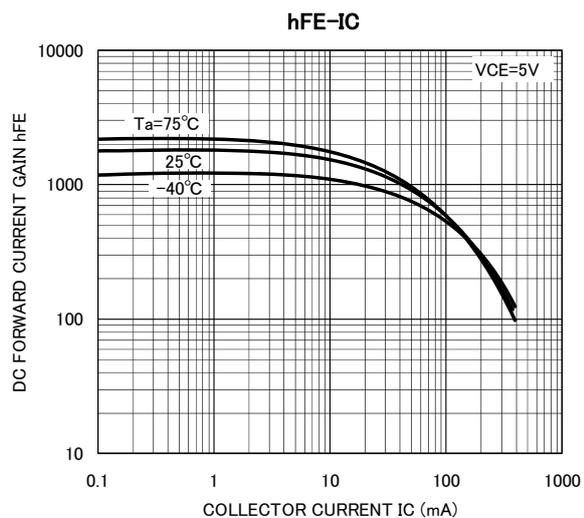
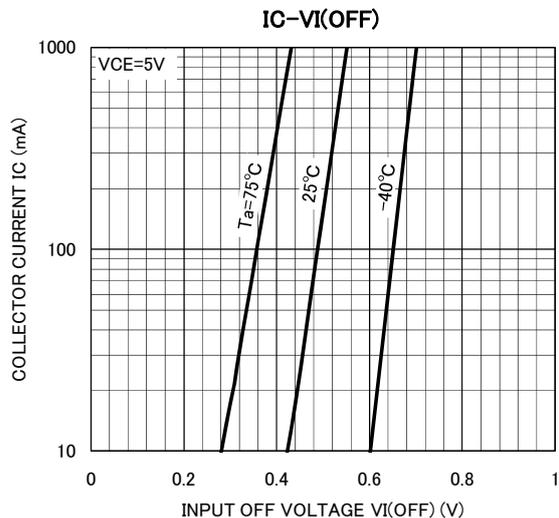
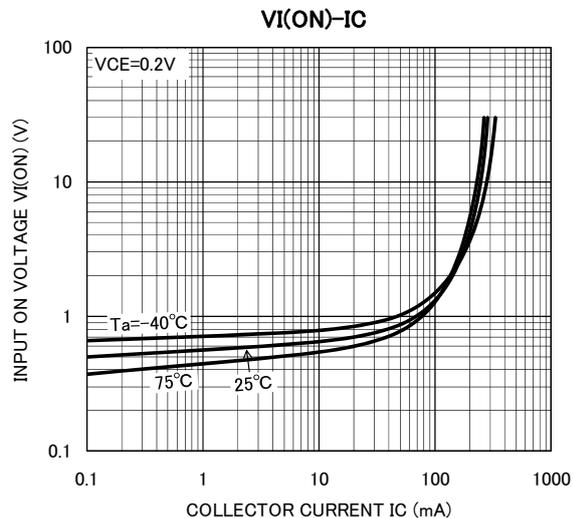
ELECTRICAL CHARACTERISTICS (Ta=25°C)(RT1, RT2 Common)

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|---------------|--------------------------------------|-----------------------------------|--------|------|------|-----------|
| | | | Min | Typ | Max | |
| V_{CBO} | Collector-base breakdown voltage | $I_C=50\mu A, I_E=0mA$ | 40 | - | - | V |
| V_{EBO} | Emitter-base breakdown voltage | $I_E=50\mu A, I_C=0mA$ | 40 | - | - | V |
| V_{CEO} | Collector-emitter breakdown voltage | $I_C=1mA, R_{BE}=\infty$ | 20 | - | - | V |
| I_{CBO} | Collector cutoff current | $V_{CB}=40V, I_E=0mA$ | - | - | 0.5 | μA |
| I_{EBO} | Emitter cutoff current | $V_{EB}=40V, I_C=0mA$ | - | - | 0.5 | μA |
| h_{FE} | DC current transfer ratio | $V_{CE}=5V, I_C=-10mA$ | 820 | - | 2500 | - |
| $V_{CE(sat)}$ | Collector-emitter saturation voltage | $I_C=10mA, I_B=0.5mA$ | - | 10 | - | mV |
| R_1 | Input resistance | - | 1.54 | 2.2 | 2.86 | $k\Omega$ |
| f_T | Transition frequency | $V_{CE}=10V, I_E=-10mA, f=100MHz$ | - | 40 | - | MHz |
| R_{ON} | Output On-resistor | $V_I=5V, f=1MHz$ | - | 0.70 | - | Ω |

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TYPICAL CHARACTERISTICS (RT_{r1}, RT_{r2} Common)





Keep safety first in your circuit designs!

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